

**Notice of References Cited**

Application/Control No.

09/807,515

Applicant(s)/Patent Under  
Reexamination  
HERBERT ET AL.

Examiner

Donghee Kang

Art Unit

2811

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**U.S. PATENT DOCUMENTS**

| * |   | Document Number<br>Country Code-Number-Kind Code | Date<br>MM-YYYY | Name | Classification |
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|   | A | US-  |                 |      |                |
|   | B | US-  |                 |      |                |
|   | C | US-  |                 |      |                |
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**FOREIGN PATENT DOCUMENTS**

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|   | V |  |
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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
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